## NSN 5961-01-317-7762

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-317-7762 **Inclosure Material:** Ceramic **Overall Length:** Between 0.690 inches and 0.770 inches **Overall Height:** 0.175 inches **Overall Width:** 0.325 inches **End Application:** Aircraft f-14 **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 100.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor and 20.0 gate to source voltage all transistor **Power Rating Per Characteristic:** 1.4 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 14 pin **Specification Data:** 81349-mil-prf-19500/599 government specification Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig:

Mil-std (military Standard):

Mil-prf-19500 spec.

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